

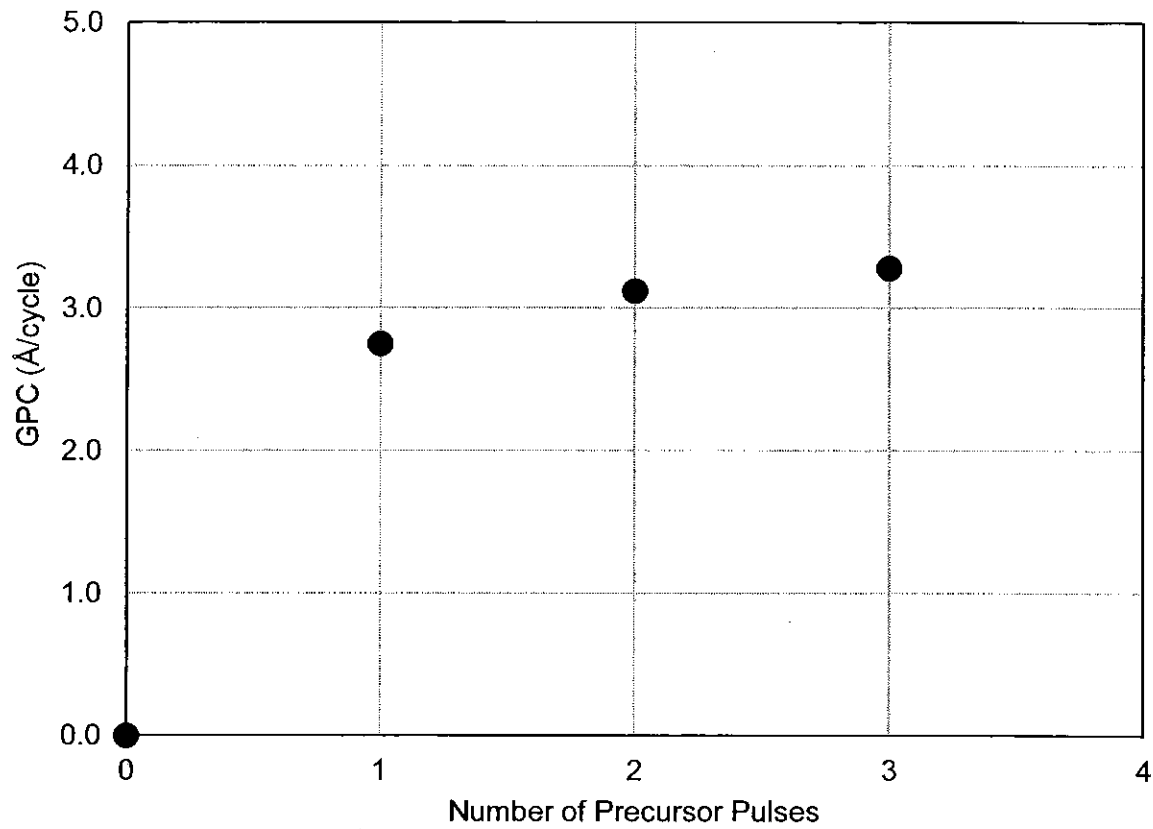


Figure 1. Thermal ALD GPC versus number of precursor pulses of 2-dimethylamino-2,4,6,8-tetramethylcyclotetrasiloxane with ozone process at 300 °C.

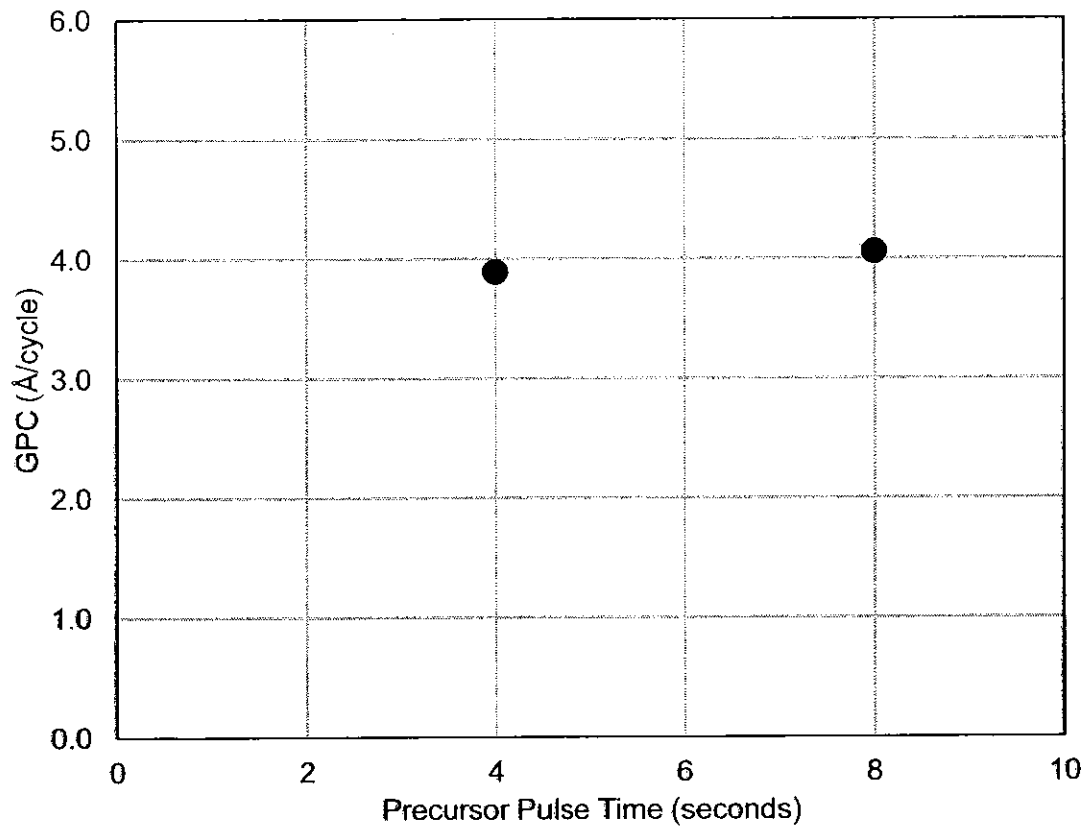


Figure 2. PEALD silicon oxide deposition GPC versus precursor pulse time with 2-dimethylamino-2,4,6,8- tetramethylcyclotetrasiloxane

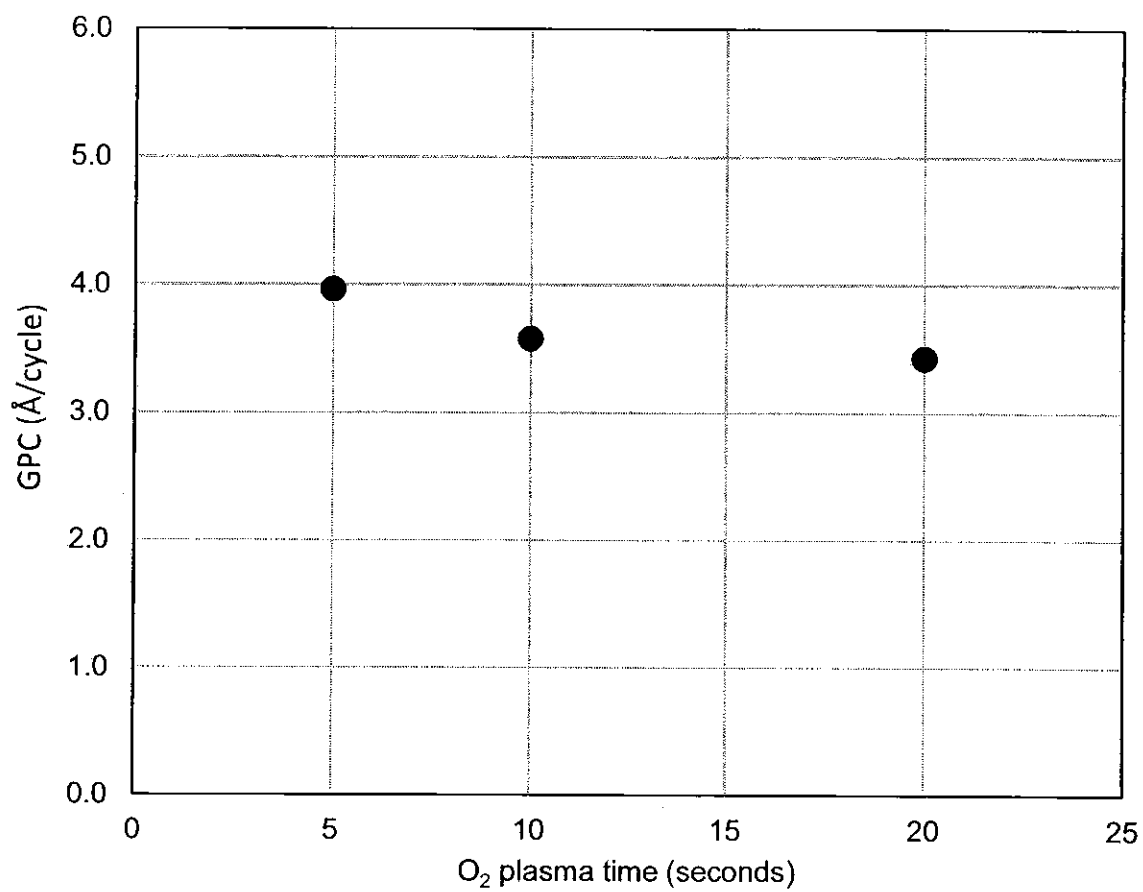


Figure 3. PEALD silicon oxide deposition GPC versus O₂ plasma exposure time with 2-dimethylamino-2,4,6,8- tetramethylcyclotetrasiloxane

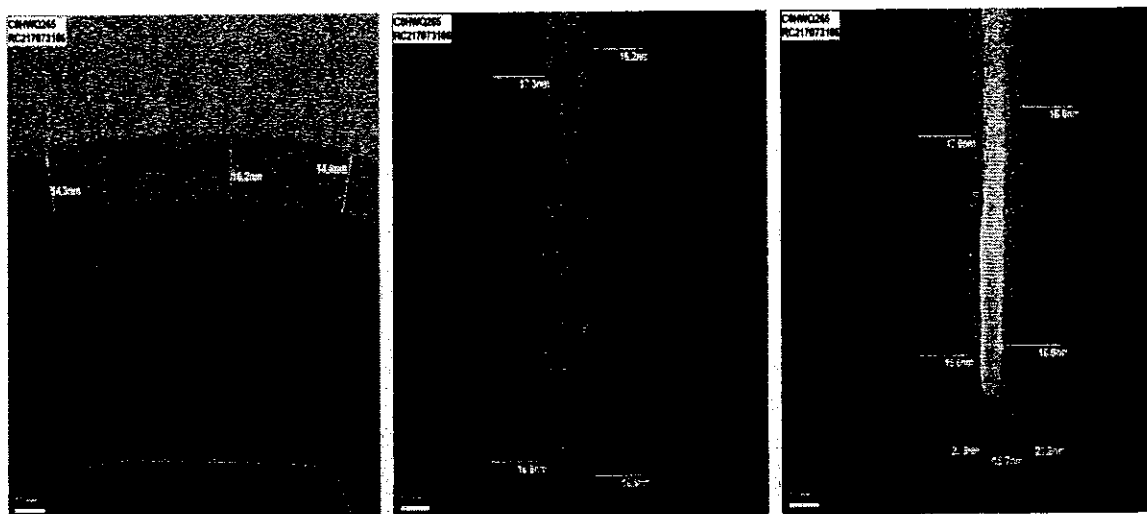


Figure 4. TEM image of silicon oxide film deposited by 2-dimethylamino-2,4,6,8-tetramethylcyclotetrasiloxane in laminar flow reactor

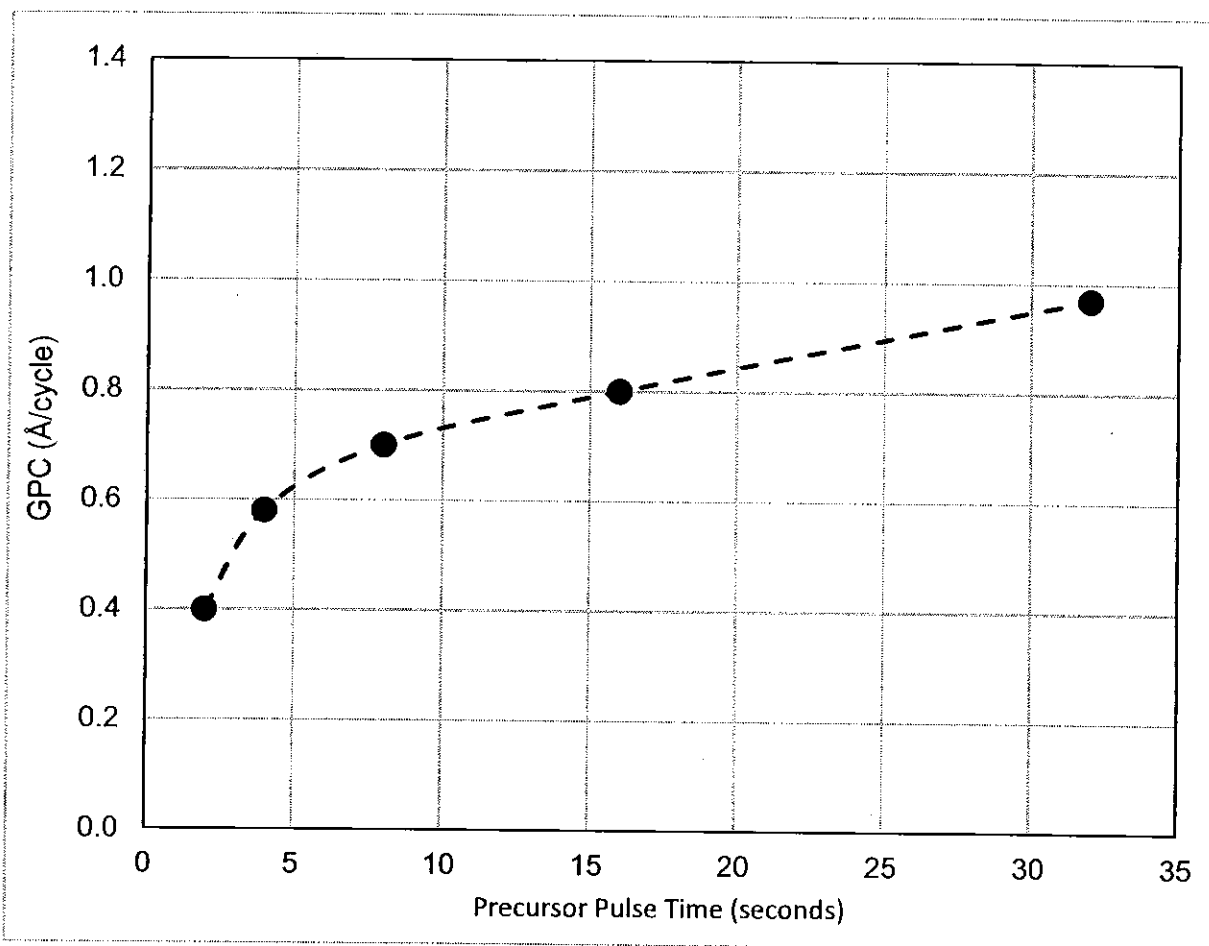


Figure 5. PEALD silicon oxide deposition GPC versus precursor pulse time with TMCTS in Showerhead Chamber.

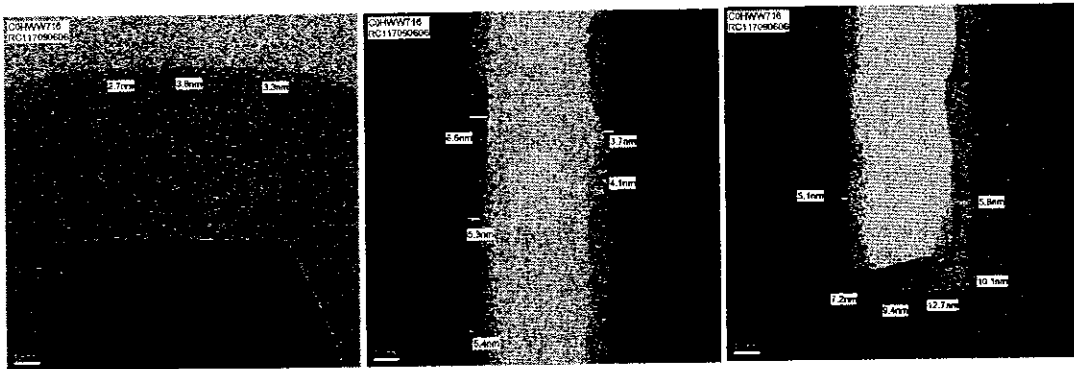


Figure 6. TEM image of silicon oxide film deposited by TMCTS in shower head chamber

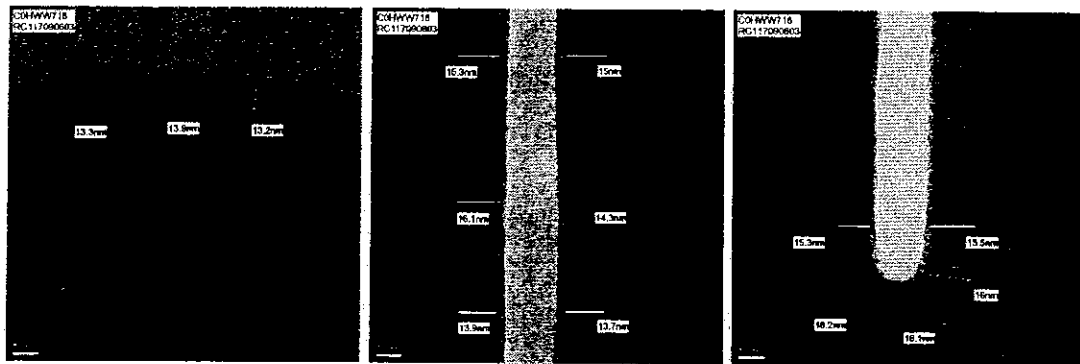


Figure 7. TEM image of silicon oxide film deposited by 2-dimethylamino-2,4,6,8-tetramethylcyclotetrasiloxane in shower head chamber.

